

INCHANGE SEMICONDUCTOR

Isc N-Channel MOSFET Transistor

STP22NM60N

FEATURES

- · Low input capacitance and gate charge
- Low gate input resistances
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

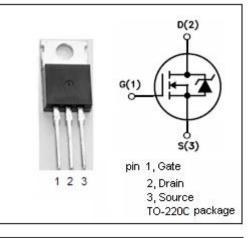
Switching applications

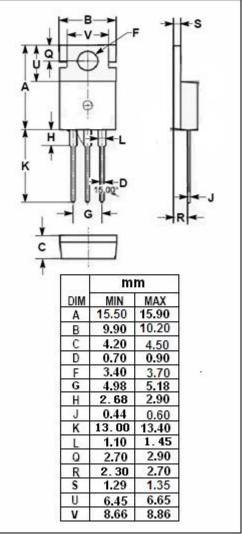
| • ABSOLUTE MAXIMUM RATINGS(Ta=25 C) | | | | | | | |
|-------------------------------------|--|----------|------|--|--|--|--|
| SYMBOL | PARAMETER | VALUE | UNIT | | | | |
| V _{DSS} | Drain-Source Voltage | 600 | V | | | | |
| V _{GSS} | Gate-Source Voltage | ±30 | V | | | | |
| I _D | Drain Current-Continuous@Tc=25℃ Tc=100℃ | 16 10 | А | | | | |
| I _{DM} | Drain Current-Single Pulsed | 64 | А | | | | |
| P _D | Total Dissipation | 125 | W | | | | |
| Tj | Operating Junction Temperature -55~150 | | °C | | | | |
| T _{stg} | Storage Temperature | -55~150 | °C | | | | |

• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | МАХ | UNIT | |
|-----------|---------------------------------------|------|--------------|--|
| Rth(ch-c) | Channel-to-case thermal resistance | 1.0 | °C /W | |
| Rth(ch-a) | Channel-to-ambient thermal resistance | 62.5 | °C/W | |





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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | MAX | UNIT |
|----------------------|--------------------------------|---|-----|-----|----------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D = 1mA | 600 | | | V |
| V _{GS} (th) | Gate Threshold Voltage | V _{DS} =±30V; I _D =0.25mA | 2 | | 4 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =8A | | 200 | 220 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±25V;V _{DS} =0V | | | ±0.1 | μ Α |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = 600V; V _{GS} = 0V; TJ=25℃ TJ=125℃ | | | 1 100 | μA |
| V _{SDF} | Diode forward voltage | I _{SD} =16A, V _{GS} = 0 V | | | 1.6 | v |

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